

2SA1201 TRANSISTOR (PNP)**FEATURES**

Power dissipation

$$P_{CM} : 500 \text{ mW (Tamb=25}^{\circ}\text{C)}$$

Collector current

$$I_{CM} : -800 \text{ mA}$$

Collector-base voltage

$$V_{(BR)CBO} : -120 \text{ V}$$

Operating and storage junction temperature range

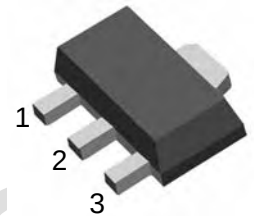
$$T_J, T_{stg}: -55^{\circ}\text{C to } +150^{\circ}\text{C}$$

SOT-89

1. BASE

2. COLLECTOR

3. EMITTER

**ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)**

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -1\text{mA}, I_E = 0$	-120			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -10\text{mA}, I_B = 0$	-120			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -1\text{mA}, I_C = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -120\text{V}, I_E = 0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5\text{V}, I_C = 0$			-0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = -5\text{V}, I_C = -100\text{mA}$	80		240	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -500\text{mA}, I_B = -50\text{mA}$			-1	V
Base-emitter voltage	V_{BE}	$V_{CE} = -5\text{V}, I_C = -500\text{mA}$			-1	V
Transition frequency	f_T	$V_{CE} = -5\text{V}, I_C = -100\text{mA}$		120		MHz
Collector output capacitance	C_{ob}	$V_{CB} = -10\text{V}, I_E = 0, f = 1\text{MHz}$			30	pF

CLASSIFICATION OF $h_{FE(1)}$

Rank	O	Y
Range	80-160	120-240
Marking	DO	DY